

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	IS&R	L1	10	("4577215") or ("5266339") or ("4357635") or ("5287536") or ("5414227") or ("5191444") or ("4547000") or ("5187533") or ("5216289") or ("5594445").PN.	USPAT; US-PGPUB	2002/07/12 09:30
2	IS&R	L2	39	("5479932") or ("5973171") or ("5145124") or ("6213115") or ("4442117") or ("4333941") or ("4359711") or ("5265153") or ("5471181") or ("5513143") or ("5513393") or ("5538637") or ("5697115") or ("5694156") or ("5751635") or ("5751450") or ("5811893") or ("5811454") or ("5811561") or ("5833968") or ("5834111") or ("5835000") or ("5844591") or ("5877111") or ("5811100") or ("5811100") or ("5840011") or ("4513597") or ("4591120") or ("4611870") or ("4994131") or ("4993097") or	USPAT; US-PGPUB	2002/07/12 09:30
3	BRS	L6	12	5 not in or 1	USPAT; US-PGPUB	2002/07/12 09:43
4	IS&R	L5	12	("5070132") or ("5095344") or ("5415541") or ("5143063") or ("5461057") or ("5313401") or ("5312180") or ("6022761") or ("4022650") or ("5713411") or ("5043940") or ("5172318") or ("5951881").PN.	USPAT; US-PGPUB	2002/07/12 09:43

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 5216269 A	19920601	13	Electrically-programmable semiconductor memory with buried injector region	257/319	257/320; 365/185.13; 365/185.31	Middelhoek, Jan et al.
2	US 4577215 A	19860318	8	Dual word line, electrically alterable, nonvolatile floating gate memory device	257/319	265/185.14; 365/185.18	Stewart, Roger G. et al.
3	US 6240015 B1	19990229	14	Method for reading 2-bit ETOX cells using gate induced drain leakage current	365/185.14	265/185.01; 365/185.26	Chi, Min-hua et al.
4	US 6112100 B1	19990403	22	Nonvolatile memory cell and method for programming and/or verifying the same	365/185.14	265/185.03; 365/185.27; 365/185.22; 365/185.26	Chen, Weong Lim
5	US 6034892 A	19990307	23	Nonvolatile memory cell and method for programming and/or verifying the same	365/185.14	265/185.01; 365/185.28	Chen, Weong Lim
6	US 5751035 A	19990512	79	Read circuits for analog memory cells	365/185.19	327/93; 327/94; 365/185.03; 365/185.27; 365/185.21	Wong, Sau C. et al.
7	US 5387534 A	19950207	11	Method of forming an array of non-volatile sense memory cells and array of non-volatile sense memory cells	438/287	438/296; 438/302	Prall, Kirk
8	US 5218569 A	19930608	23	Electrically alterable non volatile memory with n bits per memory cell	365/185.21	365/185.19; 365/185.2; 365/185.22; 365/185.29; 365/186; 365/45	Banks, Gerald

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1	US 6202262 B1	20010424	37	Multi-state memory	365/185.09	365/185.09; 365/185.11; 365/185.13	Guterman, Daniel C. et al.
2	US 5851881 A	19981222	18	Method of making memory flash memory for multi-level logic	438/298	438/298	Lin, Ruel et al.
3	US 5313441 A	19940517	28	EEPROM with split gate source side injection	365/185.13	365/185.13; 365/185.14; 365/185.15; 365/185.16; 365/185.17; 365/185.18; 365/185.19	Guterman, Daniel C. et al.
4	US 5172429 A	19921215	44	Multi-state EEPROM read and write circuits and techniques	365/185.03	365/185.03; 365/185.04; 365/185.05; 365/185.06; 365/185.07; 365/185.08; 365/185.09; 365/185.10; 365/185.11; 365/185.12; 365/185.13; 365/185.14; 365/185.15; 365/185.16; 365/185.17; 365/185.18; 365/185.19; 365/185.20; 365/185.21; 365/185.22; 365/185.23; 365/185.24; 365/185.25; 365/185.26; 365/185.27; 365/185.28; 365/185.29; 365/185.30; 365/185.31; 365/185.32; 365/185.33; 365/185.34; 365/185.35; 365/185.36; 365/185.37; 365/185.38; 365/185.39; 365/185.40; 365/185.41; 365/185.42; 365/185.43; 365/185.44; 365/185.45; 365/185.46; 365/185.47; 365/185.48; 365/185.49; 365/185.50; 365/185.51; 365/185.52; 365/185.53; 365/185.54; 365/185.55; 365/185.56; 365/185.57; 365/185.58; 365/185.59; 365/185.60; 365/185.61; 365/185.62; 365/185.63; 365/185.64; 365/185.65; 365/185.66; 365/185.67; 365/185.68; 365/185.69; 365/185.70; 365/185.71; 365/185.72; 365/185.73; 365/185.74; 365/185.75; 365/185.76; 365/185.77; 365/185.78; 365/185.79; 365/185.80; 365/185.81; 365/185.82; 365/185.83; 365/185.84; 365/185.85; 365/185.86; 365/185.87; 365/185.88; 365/185.89; 365/185.90; 365/185.91; 365/185.92; 365/185.93; 365/185.94; 365/185.95; 365/185.96; 365/185.97; 365/185.98; 365/185.99; 365/186.00	Mehrotra, Rajiv et al.
5	US 5095044 A	19920310	49	Highly compact EPROM and flash EPROM devices	257/328	257/327; 257/488; 365/185.03; 365/185.04; 365/185.05; 365/185.06; 365/185.07; 365/185.08; 365/185.09; 365/185.10; 365/185.11; 365/185.12; 365/185.13; 365/185.14; 365/185.15; 365/185.16; 365/185.17; 365/185.18; 365/185.19; 365/185.20; 365/185.21; 365/185.22; 365/185.23; 365/185.24; 365/185.25; 365/185.26; 365/185.27; 365/185.28; 365/185.29; 365/185.30; 365/185.31; 365/185.32; 365/185.33; 365/185.34; 365/185.35; 365/185.36; 365/185.37; 365/185.38; 365/185.39; 365/185.40; 365/185.41; 365/185.42; 365/185.43; 365/185.44; 365/185.45; 365/185.46; 365/185.47; 365/185.48; 365/185.49; 365/185.50; 365/185.51; 365/185.52; 365/185.53; 365/185.54; 365/185.55; 365/185.56; 365/185.57; 365/185.58; 365/185.59; 365/185.60; 365/185.61; 365/185.62; 365/185.63; 365/185.64; 365/185.65; 365/185.66; 365/185.67; 365/185.68; 365/185.69; 365/185.70; 365/185.71; 365/185.72; 365/185.73; 365/185.74; 365/185.75; 365/185.76; 365/185.77; 365/185.78; 365/185.79; 365/185.80; 365/185.81; 365/185.82; 365/185.83; 365/185.84; 365/185.85; 365/185.86; 365/185.87; 365/185.88; 365/185.89; 365/185.90; 365/185.91; 365/185.92; 365/185.93; 365/185.94; 365/185.95; 365/185.96; 365/185.97; 365/185.98; 365/185.99; 365/186.00	Harari, Ellyahou
6	US 5043540 A	19910817	14	Flash EEPROM memory systems having multistate storage cells	365/185.03	365/185.03; 365/185.04; 365/185.05; 365/185.06; 365/185.07; 365/185.08; 365/185.09; 365/185.10; 365/185.11; 365/185.12; 365/185.13; 365/185.14; 365/185.15; 365/185.16; 365/185.17; 365/185.18; 365/185.19; 365/185.20; 365/185.21; 365/185.22; 365/185.23; 365/185.24; 365/185.25; 365/185.26; 365/185.27; 365/185.28; 365/185.29; 365/185.30; 365/185.31; 365/185.32; 365/185.33; 365/185.34; 365/185.35; 365/185.36; 365/185.37; 365/185.38; 365/185.39; 365/185.40; 365/185.41; 365/185.42; 365/185.43; 365/185.44; 365/185.45; 365/185.46; 365/185.47; 365/185.48; 365/185.49; 365/185.50; 365/185.51; 365/185.52; 365/185.53; 365/185.54; 365/185.55; 365/185.56; 365/185.57; 365/185.58; 365/185.59; 365/185.60; 365/185.61; 365/185.62; 365/185.63; 365/185.64; 365/185.65; 365/185.66; 365/185.67; 365/185.68; 365/185.69; 365/185.70; 365/185.71; 365/185.72; 365/185.73; 365/185.74; 365/185.75; 365/185.76; 365/185.77; 365/185.78; 365/185.79; 365/185.80; 365/185.81; 365/185.82; 365/185.83; 365/185.84; 365/185.85; 365/185.86; 365/185.87; 365/185.88; 365/185.89; 365/185.90; 365/185.91; 365/185.92; 365/185.93; 365/185.94; 365/185.95; 365/185.96; 365/185.97; 365/185.98; 365/185.99; 365/186.00	Harari, Ellyahou

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1	US 5838041 A	19981117	15	Nonvolatile semiconductor memory device having memory cell transistor with effect region acting as a charge carrier injecting region	257/324	257/326	Sakagami, Eiji et al.
2	US 5854568 A	19990905	24	Semiconductor device including nonvolatile memories	257/324	257/295; 257/314; 257/326	Nakano, Hiroshi
3	US 4461527 A	19841106	8	High density MNOS transistor with ion implant into nitride layer adjacent gate electrode	257/325	257/326; 257/394; 257/395; 365/178; 365/184	Chen, Yung J. et al.
4	US 4342099 A	19800727	9	Electrically erasable programmable MNOS read only memory	365/104	257/326; 365/184	Pao, Chang Piang
5	US 4057820 A	19771108	15	Dual gate MNOS transistor	257/326	148/DIG.156	Gallagher, Robert C.
6	US 3925804 A	19751209	17	Structure of and the method of processing a semiconductor matrix or MNOS memory elements	257/326	326/106	Gracchi, James Ronald et al.

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